# In the claims:

## 1. (Currently amended)

A method of manufacturing a plurality of micro enclosures on a substrate wafer, comprising steps of:

- (1) bonding a cap wafer to said substrate wafer with an adhesive layer to form the top and the bottom of said micro enclosures;
- (2) patterning and etching said cap wafer and said adhesive layer to form islands of layers of said cap wafer and said adhesive layer on said substrate wafer; and
- (3) depositing and patterning at least one metal <u>and/or</u> <u>insulator</u> layer to cover the outer sidewall surfaces around on said islands, <u>including the sidewall surfaces of said cap wafer and said adhesive layer</u>, to form a sidewall <u>of said enclosures</u>. <u>sidewall around each of said islands</u>.

## 2. (Previously presented)

The method of claim 1, further comprising the steps of:

- (1) patterning and etching etch access holes in said cap wafer of said enclosures;
- (2) removing said adhesive layer through said etch access holes from said enclosures; and
  - (3) sealing said etch access holes with deposited films.

#### 3. (Canceled)

4. (Original) The method of claim 1, wherein said etching is accomplished with high-density plasma that contains hydrogen or argon.

5. (Original) The method of claim 1, wherein said substrate wafer comprises one or more of following:

micro-electro-mechanical device,

polymeric sacrificial layer,

polymeric planarizing layer,

microelectronic circuit,

and electrical component,

prior to said bonding.

## 6. (Previously presented)

The method of claim 1, further comprising a step of depositing getters on said cap wafer prior to said step (1) of bonding a cap wafer to said substrate wafer with an adhesive layer and subsequent heat activation of said getters.

## 7. (Previously presented)

The method of claim 2, wherein said deposited films comprises gas gettering materials.

## 8. (Previously presented)

The method of claim 7, wherein said gettering materials comprises  $\text{TiN}_x\text{O}_y$  and/or  $\text{TiN}_x$ .

#### 9-10. (Canceled)

## 11. (Withdrawn)

The method of claim 2, wherein in said sealing is done under controlled gas pressure environment comprising high vacuum or inert gas.

## 12. (Withdrawn)

The method of claim 2, wherein said enclosures form pressure transducers.

## 13. (Previously presented)

The method of claim  $\underline{1}$ , wherein said enclosures form vacuum or hermetic packaging for micro-electro-mechanical devices.

## 14. (Original)

The method of claim 2, wherein said removing said adhesive layer is by etching with oxygenated plasma.

## 15. (Currently amended)

Said etching in claim 14 removes organic polymer <del>coating</del> or sacrificial layer in said enclosures.

## 16. (Canceled)

#### 17. (Original)

The method of claim 1, wherein said depositing at least on metal layer is by physical vapor deposition, plating, electroplating, or chemical vapor deposition.

#### 18. (Canceled)

## 19. (Withdrawn)

The method of claim 1, further comprises planarizing said substrate wafer prior to said bonding, comprising steps of: coating said wafer with a thick epoxy layer; curing said epoxy layer by heat or ultraviolet light; and thinning said epoxy layer to the desired thickness by lapping, grinding or polishing.

#### 20. (Withdrawn)

The method of claim 19, wherein said thick epoxy layer fills holes, cavities, troughs, or underside space of suspended structures.

#### 21. (Withdrawn)

The method of claim 20, further comprising the step of placing said wafer under a vacuum during or after said coating.

#### 22-27. (Canceled)

#### 28. (Original)

The method of claim 1, wherein said adhesive layer is disposed by spinning and said spinning is at speed of between 1500 rpm to 7000 rpm for less than 2 seconds.

#### 29. (Original)

The method of claim 1, wherein said adhesive layer comprises Abocast 50-24 epoxy resin from Abatron, Incorporated, Kenosha, WI 53144 USA.

#### 30. (Canceled)